

Optical Parameters from Tuning electronic and conductivity features of Multilayer WTe₂ using point defects

Ilkay Ozdemir,¹ Christoph Kastl,^{2,3} Alexander W. Holleitner,^{2,3} and Olcay Üzengi Aktürk^{4,2}

¹*Physics Department, Adnan Menderes University, Aydin 09100, Turkey.*

²*Walter Schottky Institut and Physics Department,*

Technical University of Munich, Am Coulombwall 4a, 85748 Garching, Germany.

³*Munich Center of Quantum Science and Technology (MCQST), Schellingstr. 4, 80799 Munich, Germany.*

⁴*Electrical and Electronic Engineering Department,
Adnan Menderes University, 09100 Aydin, Turkey*

We investigate electronic, optical and thermoelectric features of monolayer and multilayer 1T' WTe₂ by *ab initio* calculations based on spin-polarized density functional theory (DFT). We used Vasp package [1, 2] for optical calculations, where the imaginary part of the dielectric constant (ε_2) can be obtained by a summation over empty states using the following equation:

$$\begin{aligned} \varepsilon_2^{\alpha\beta}(\omega) = & \frac{4\pi^2 e^2}{\Omega} \lim_{q \rightarrow 0} \frac{1}{q^2} \sum_{c,v,\mathbf{k}} 2\omega_{\mathbf{k}} \delta(\epsilon_{c\mathbf{k}} - \epsilon_{v\mathbf{k}} - \omega) \\ & \times \langle u_{c\mathbf{k}+e_\alpha\mathbf{q}} | u_{v\mathbf{k}} \rangle \langle u_{c\mathbf{k}+e_\beta\mathbf{q}} | u_{v\mathbf{k}} \rangle^* \end{aligned} \quad (1)$$

Here, c and v represent the conduction and valence band states, and $u_{c\mathbf{k}}$ represents the periodicity of the wave function at the \mathbf{k} -point, respectively. The real part of the dielectric constant (ε_1) can be obtained by the Kramers-Kronig transformation [3] as follows:

$$\varepsilon_1^{\alpha\beta}(\omega) = 1 + \frac{2}{\pi} P \int_0^\infty \frac{\epsilon_2^{\alpha\beta}(\omega') \omega'}{\omega'^2 - \omega^2 + i\eta} d\omega' \quad (2)$$

The total frequency dependent complex dielectric constant is then the sum of these two terms as $\varepsilon(\omega) = \varepsilon_1(\omega) + i\varepsilon_2(\omega)$.

With the frequency dependent complex dielectric constant, we can calculate the optical conductivity ($\sigma(\omega)$), absorbance ($A(\omega)$), extinction coefficient ($k(\omega)$), refractive index ($n(\omega)$) according to: [4]

$$\sigma(\omega) = \sigma_1(\omega) + i\sigma_2(\omega) = -i \frac{\omega}{4\pi} [\varepsilon_1(\omega) + i\varepsilon_2(\omega) - 1] \quad (3)$$

$$A(\omega) = \frac{\omega}{c} \varepsilon_2(\omega) \Delta z \quad (4)$$

$$k(\omega) = \frac{1}{\sqrt{2}} \left\{ [\varepsilon_1^2(\omega) + \varepsilon_2^2(\omega)]^{\frac{1}{2}} - \varepsilon_1(\omega) \right\}^{\frac{1}{2}} \quad (5)$$

$$n(\omega) = \frac{1}{\sqrt{2}} \left\{ [\varepsilon_1^2(\omega) + \varepsilon_2^2(\omega)]^{\frac{1}{2}} + \varepsilon_1(\omega) \right\}^{\frac{1}{2}} \quad (6)$$

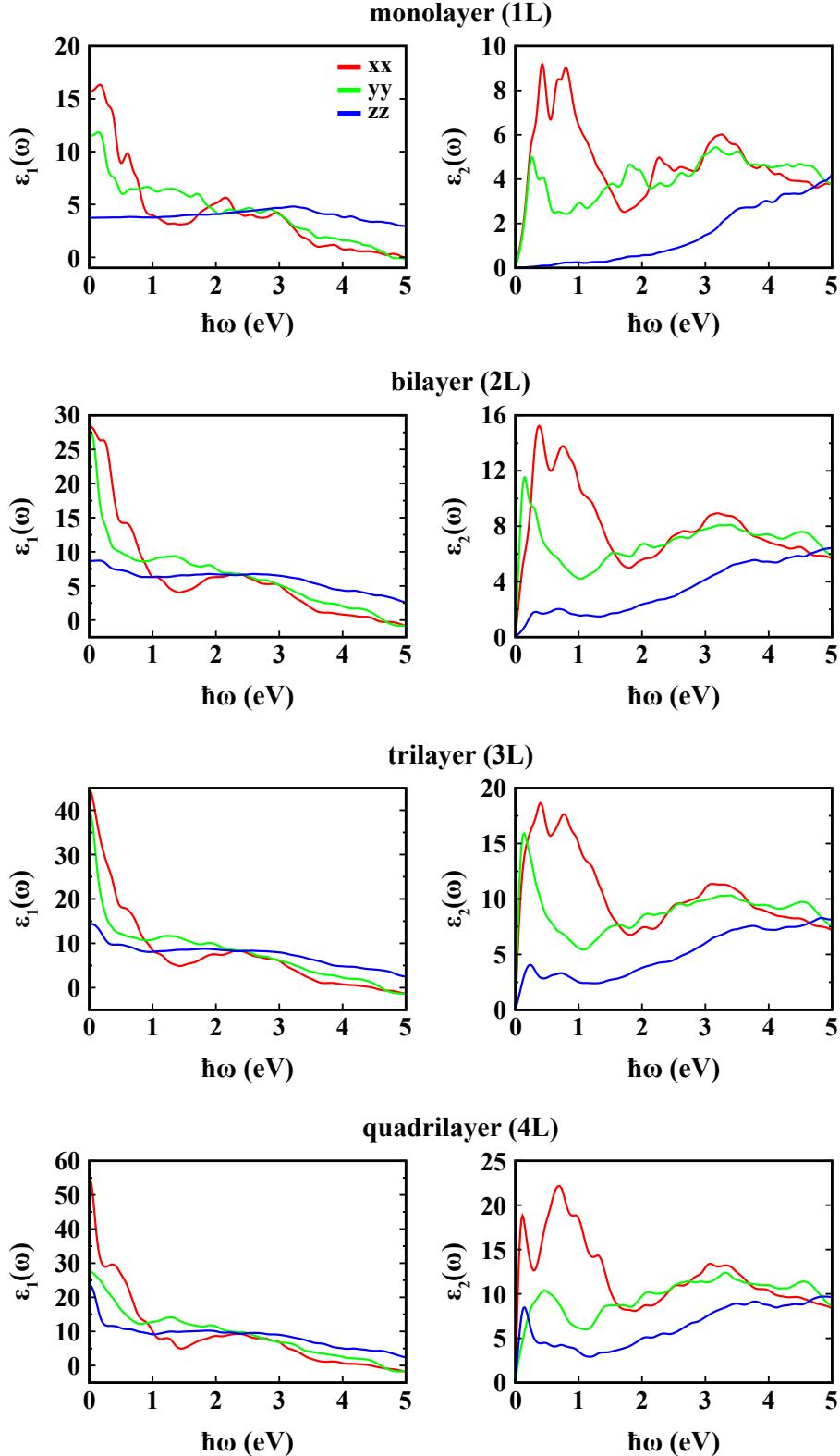


FIG. 1. Real ($\varepsilon_1(\omega)$) and imaginary ($\varepsilon_2(\omega)$) parts of frequency dependent dielectric constant calculated for 1L-to-4L 1T' WTe₂ as a function of photon energy ($\hbar\omega$) at 0 K along crystallographic axes (xx , yy , zz).

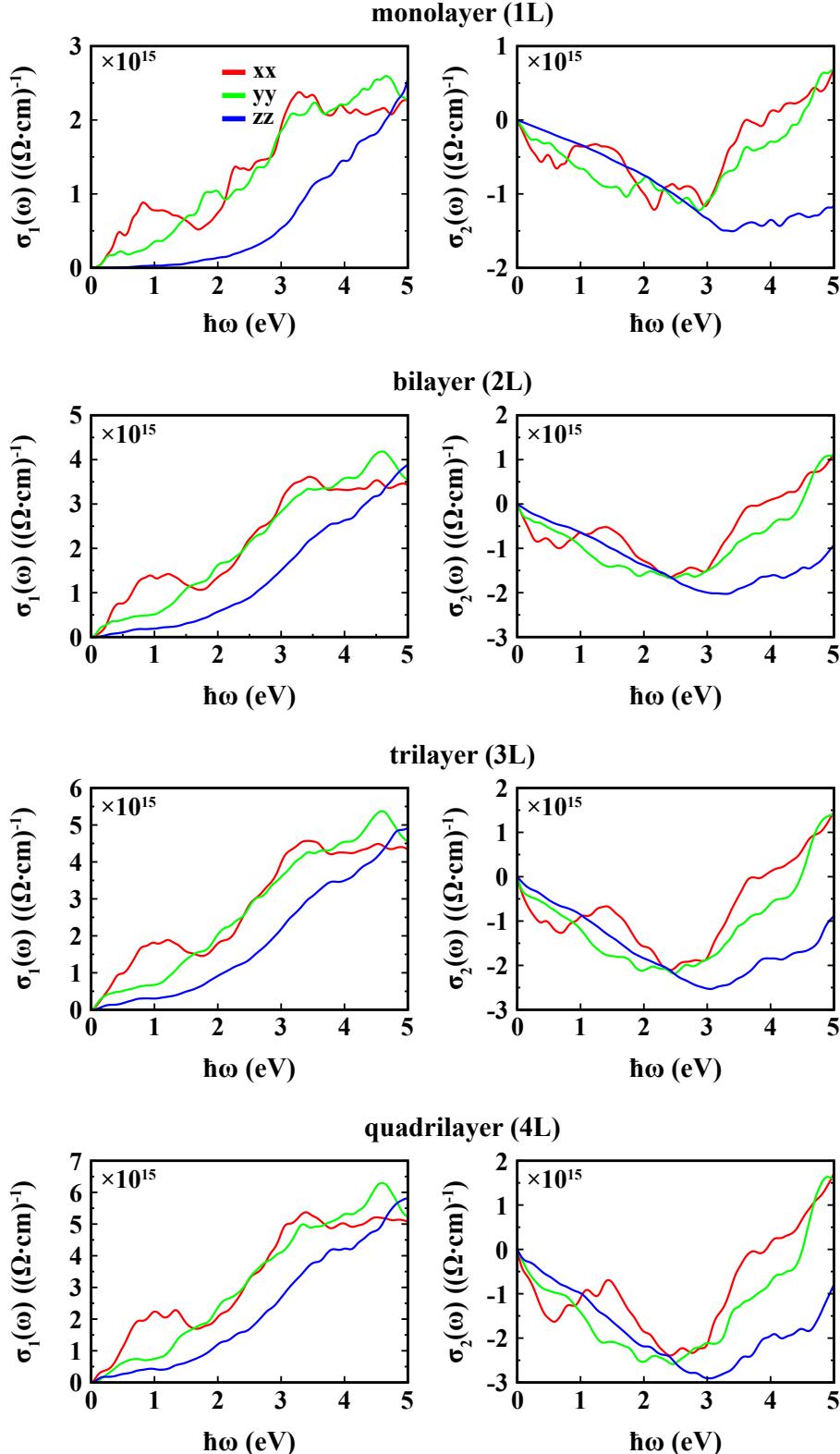


FIG. 2. Real ($\sigma_1(\omega)$) and imaginary ($\sigma_2(\omega)$) parts of frequency dependent optical conductivity calculated for 1L-to-4L 1T' WTe₂ as a function of photon energy ($\hbar\omega$) at 0K along crystallographic axes (xx, yy, zz).

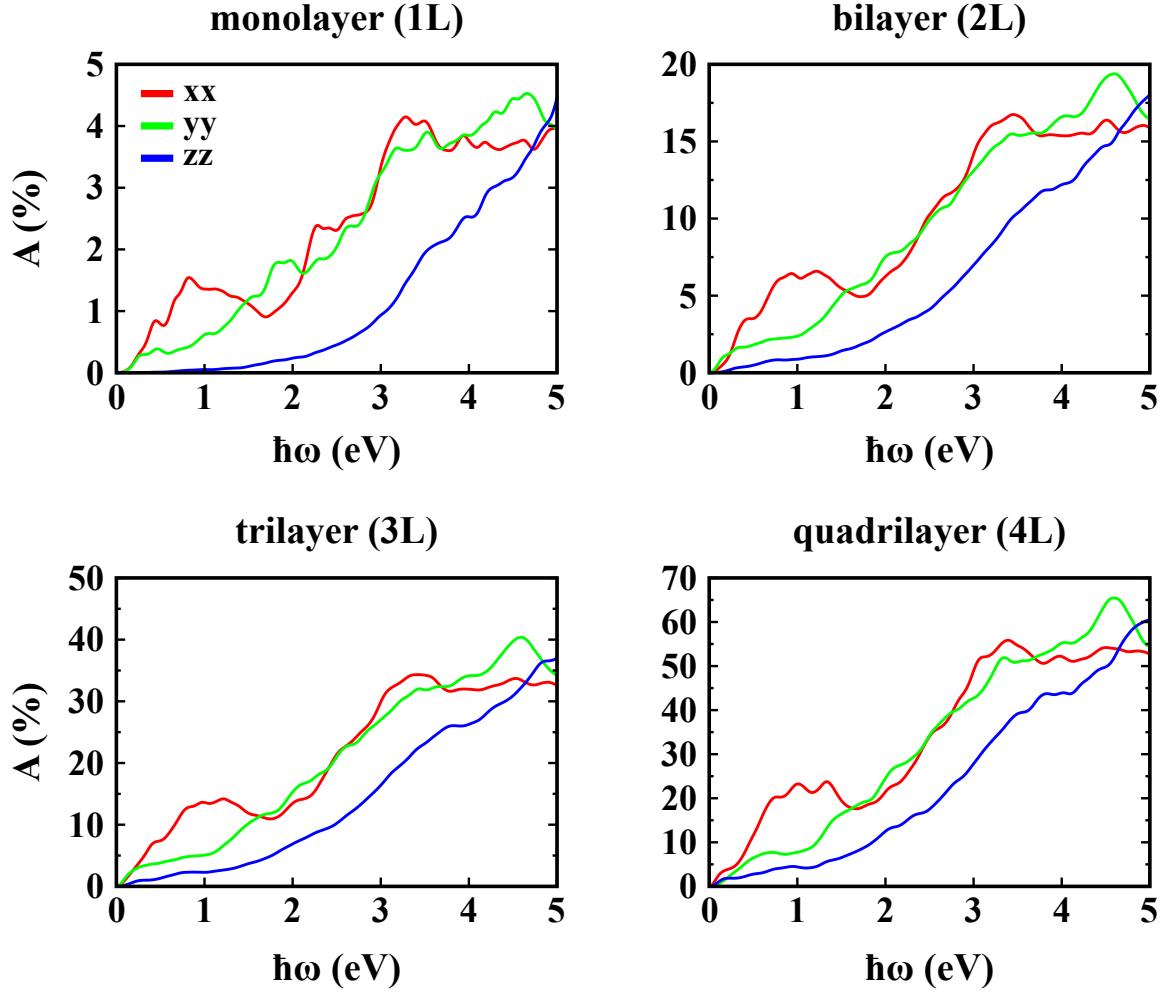


FIG. 3. Frequency dependent absorbance ($A(\omega)$) calculated for 1L-to-4L 1T' WTe_2 as a function of photon energy ($\hbar\omega$) at 0 K along crystallographic axes (xx , yy , zz).

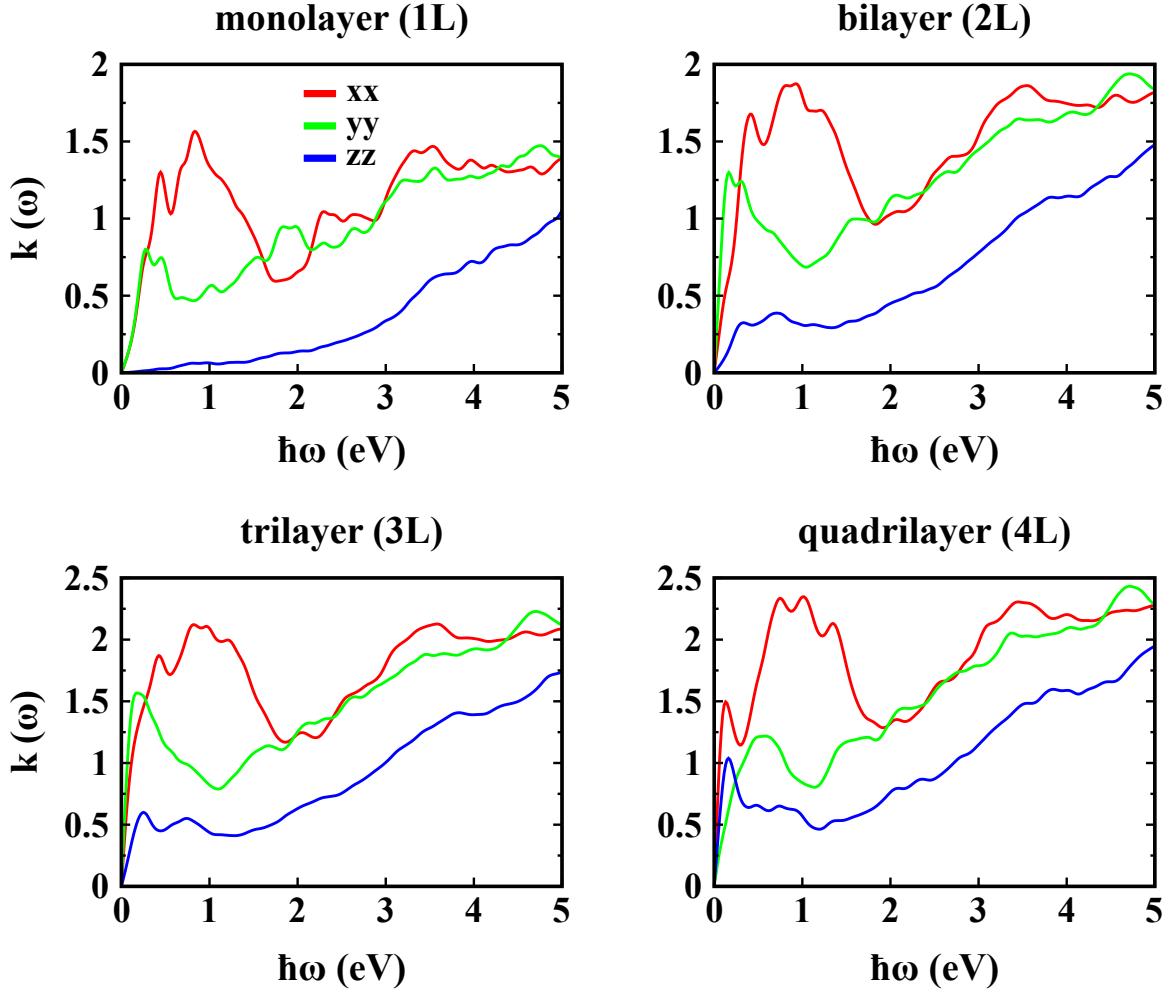


FIG. 4. Frequency dependent extinction coefficient ($k(\omega)$) calculated for 1L-to-4L 1T' WTe₂ as a function of photon energy ($\hbar\omega$) at 0 K along crystallographic axes (xx , yy , zz).

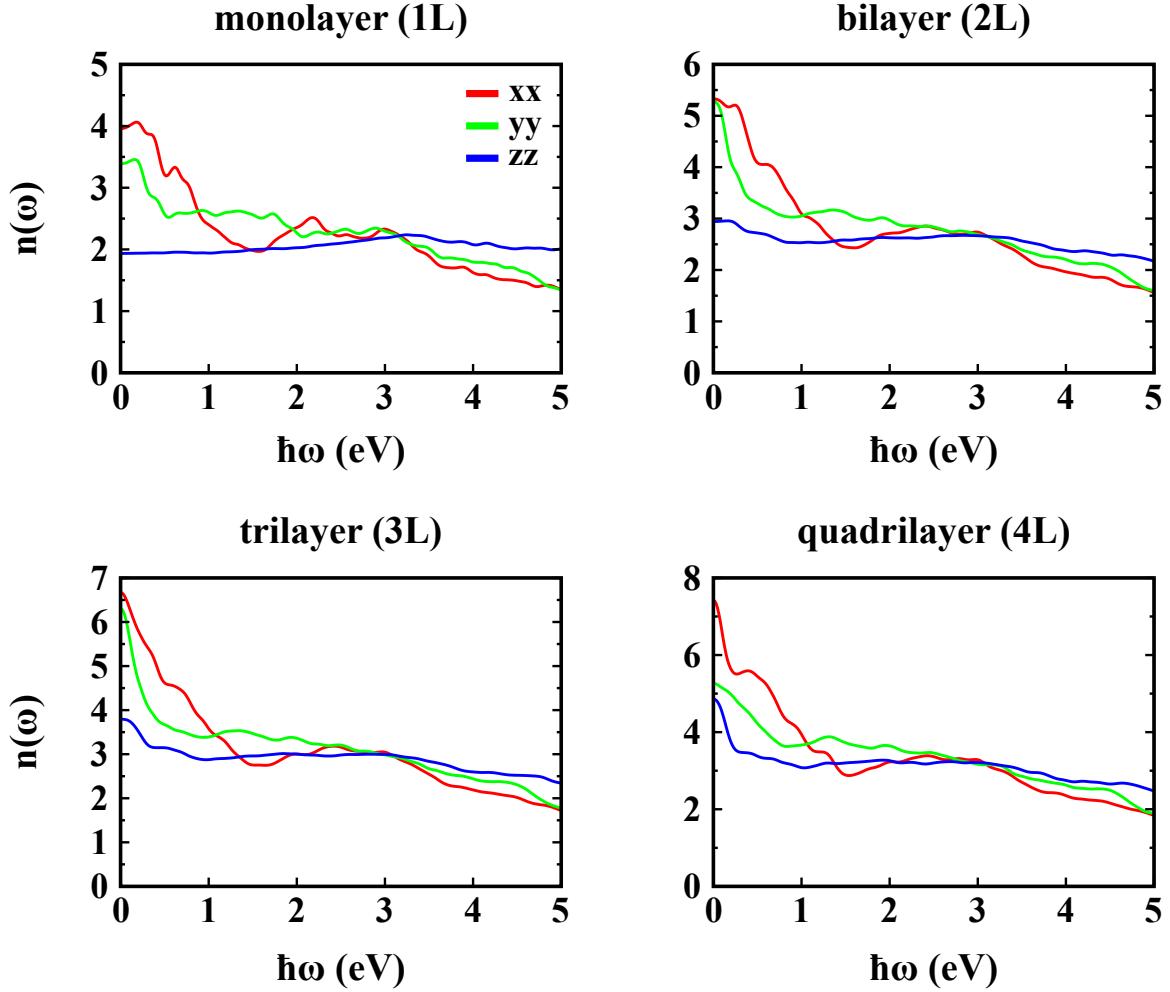


FIG. 5. Frequency dependent refractive index ($n(\omega)$) calculated for 1L-to-4L 1T' WTe₂ as a function of photon energy ($\hbar\omega$) at 0 K along crystallographic axes (xx , yy , zz).

-
- [1] Georg Kresse and Jürgen Furthmüller, “Efficiency of ab-initio total energy calculations for metals and semiconductors using a plane-wave basis set,” *Computational Materials Science* **6**, 15–50 (1996).
 - [2] Georg Kresse and Jürgen Furthmüller, “Efficient iterative schemes for ab initio total-energy calculations using a plane-wave basis set,” *Physical Review B* **54**, 11169 (1996).
 - [3] M Gajdoš, K Hummer, G Kresse, J Furthmüller, and F Bechstedt, “Linear optical properties in the projector-augmented wave methodology,” *Physical Review B* **73**, 045112 (2006).
 - [4] Yelda Kadioglu, “Ballistic transport and optical properties of a new half-metallic monolayer: Vanadium phosphide,” *Materials Science and Engineering: B* **268**, 115111 (2021).